

Introduction to Transmission Electron Microscopy (II)

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Scanning Transmission Electron Microscopy

Convergent / Focused Beam



Scanning TEM (STEM)

• Basic STEM imaging

- Aberration corrected STEM
- Analytical STEM

Electron beam interaction with a thin specimen



- Energy Loss & very small scattering angle
 - Incoherent (longer wavelength)

Scattered electrons are collected for imagining depending on the scattering angle with detectors of different shapes and sizes



STEM Imaging Detectors



• Bright-field (BF)

- a small disc-shaped detector
- collects on-axis forward-scattered electrons (bright disk)
- Annular dark-field (ADF) (concentric with the BF)
 - a low-medium angle annular detector
 - collects coherent elastically scattered electrons
 - diffraction contrast dominant
- High-angle annular dark-field (HAADF)
 - a large angle annular detector
 - collects incoherent elastically scattered electrons
 - z contrast only (~ z²)
- Segmented detector
 - Multimodal imaging
 - BF, ADF, HAADF, etc.



STEM – (HA)ADF Imaging Compared to CTEM Imaging

Iridium (Ir) nanoparticles on an amorphous carbon film



Jianguo Wen, Chapter 5 from "Practical Materials Characterization"

The tiny heavy element particles seen clearly in the STEM image but not in the TEM image.



- Chemical sensitive
- Intuitive contrast interpretation





"See" atomic columns?



Jianguo Wen, Chapter 5 "Practical Materials Characterization"

- <100> Atomic resolution HAADF image of SrTiO₃
- HAADF imaging always shows a positive contrast transfer
- The observed bright dots directly correspond to atomic columns
- Insensitive to light elements when imaged with heavy elements due to a lower scattering power of the light elements

CTEM-HR image interpretation is not straightforward

The images contrast is very sensitive to several factors, e.g., focus condition.



(LA)ADF vs. HAADF



https://www.jeol.com/words/emterms/20121023.063558.php#gsc.tab=0

STEM images of the cross-sectional thin film of a semiconductor device

- ADF works better for light elements
- ADF has diffraction contrast/strain contrast



- 1. Basics of Scanning Transmission Electron Microscopy
- 2. Aberration-corrected Scanning Transmission Electron Microscopy
- 3. Analytical Scanning/Transmission Electron Microscopy

STEM Resolution is Limited by Lens Aberration



- Spherical aberration and aperture diffraction pose a fundamental limit to the achievable probe size
- The disc of least confusion from spherical aberration is proportional to aberration coefficient Cs as well as the cube of the semi-convergence angle α
- To improve the spatial resolution, Cs needs to be addressed

Spherical Aberration Correction

The era of aberration correction : it all began in 1936...

In 1936, Scherzer proved that any electron optical system will always suffer from *spherical aberration* (*Cs*) and *chromatic aberration* (*Cc*) if simultaneously:

- the optical system is rotationally symmetric
- the system produces a real image of the object
- the fields of the system do not vary with time
- there is no charge on the axis

Breaking the rotational symmetry

 achieved by using a highly complex computer-controlled sets of multiple lenses

The idea is to introduce a corrector that produces negative lens to give a total of zero spherical aberration, i.e., the rays are re-converged to a point rather than a disk



https://www.superstem.org/learn/cs-correction



Maximilian Haider, Harald Rose & Knut Urban

https://www.agenciasinc.es/Noticias/Haider-Rose-y-Urban-premio-Fronteras-del-Conocimiento-por-inventar-el-microscopio-de-precision-subatomica

Hexapole C_s Corrector CTEM & STEM



Ondrej Krivanek Nion Company Quadrupole-Octupole C_s corrector STEM





Spherical Aberration Correction



C Chen, Themis

https://www.fei.com/products/ter //themis-z-for-materials-science/

With the 2nd generation probe corrector, high order aberrations are correctable, therefore better imager resolution, especially at lower kV, e.g., 60 kV



Integrated Differential Phase Contrast (iDPC)

- The electric field of the specimen atoms deflect the electron beam
- The intensity difference caused by the deflection is measured by a segmented detector
- The difference produces a vector image: DPC \rightarrow relate to the sample's electric field
- The DPC is integrated into a scalar image: iDPC \rightarrow electrostatic potential visualized
- The contrast of iDPC is proportional to the atomic number Z

Why it works for light atoms better than HAADF?

- The contrast of iDPC is proportional to the atomic number Z (compared to Z² in HAADF)
- HAADF collects high angle scattered electrons, but light atoms have lower probability of high angle scattering.
- iDPC collects electrons from the center transmitted disc, not high angle scattered electrons, therefore SNR is high, even for light atoms



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 $DPC_v = B - D$

Simultaneous Imaging Light Elements & Heavy elements by iDPC-STEM





Simultaneous Imaging Light Elements & Heavy elements by iDPC-STEM

GaN <211> @ 300 kV









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Analytical Transmission Electron Microscopy



STEM-EDS Compared with SEM-EDS



Williams and Carter (2nd edition)

- Higher spatial resolution
 - (~ nm compared with ~ μ m in SEM)
 - smaller incident probe
 - minimum beam broadening
- Detection sensitivity?



4-crystals detection system 0.7 steradians



- Advanced instrumentation
 - better EDS detector design
 - larger EDS collection solid angle
 - higher collection efficiency

Advanced instrumentation

- brighter electron source
- aberration correction
- smaller probe carrying higher current

Atomic resolution achievable!

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Atomic Resolution EDS Mapping with an Aberration Corrected STEM

Strontium Titanium Oxide (SrTiO₃):

elemental mapping of individual columns of atoms

Atomic mapping of light element oxygen



12 minutes acquisition time, 100pA, 300kV

C. Chen, J. Mabon, Themis Z, MRL

DCFI HAADF



✓ □ Unwanted system and spurious X-rays

- Forward and backward scattered electrons excite system X-rays in stage & pole-pieces
- Spurious X-rays elsewhere in the specimen by Bremsstrahlung (grayshaded) and system X-rays
- X-rays from support grid or TEM holder
- ✓ □ Collection efficiency is relatively low
- ✓ □ Challenging for light elements
- ✓ □ Relatively poor energy resolution

Strength of Electron Energy Loss Spectroscopy (EELS)



Modified from Williams and Carter 2009

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EELS vs. EDS

	EELS EDS						
Collection Efficiency	High (close to 100 %)	Low (1-10 %)					
Spatial Resolution	0.1 - 1 nm Atomic (with aberration correction)	0.1 nm – 10 nm Atomic (with aberration correction)					
	EELS > EDS						
Energy Resolution	~ 1 eV (better with Monochromator)	~ 130 eV (Mn Kα)					
Information Available	Atomic, chemical, electronic, optical and more	Atomic only					
Elements Light/Heavy	Excellent for light elements Signal weak in high loss region	Excellent for medium to heavy elements Low yield for light elements					
Quantification	Absolute & Relative	Relative only					
Easy to Use?	Getting easier with advanced software	Easy to use and interpret for basic applications					

Electron Energy Loss Spectroscopy (EELS)



Interact with the electron cloud of an atom

Energy Loss & Small scattering angle

EELS Electron Optical System -how are electron energies measured in EELS?



- EELS analyzes the energy distribution of electrons that have passed through the specimen
- Electrons with different energy (loss) passing through the magnetic prism bent to different angles and form a spectrum (like white light can be broken into lights of different colors by an optic prism)





Williams and Carter (2nd edition)

- An extremely high intensity zero-loss peak
- The rest of the peaks appear as small bumps (edges) sitting on a high background
- The background falls rapidly with energy loss increases
- Intensity of the entire spectrum goes across many orders of magnitude
 - Full view is only possible in log scale
- Energy resolution is much higher than that of EDS (~ 1 eV vs. ~130 eV)





https://eels.info/

Plural scattering removal/correction

From e- source energy spread, spectrometer resolution — specimen thickness, energy & intensity reference

Low-loss spectrum (< ~ 50 eV)</p>

From interactions with weakly bound outer-shell electrons (valence/conduction) of the specimen atoms

Plasmon excitation peak

Valence electron cloud deforms collectively in response to incident electron beam

- valence/conduction electron density
- Near zero-loss feature
 - Inter-band transitions (e.g., band gap)
- Low loss distribution (< ~ 50 eV)
 - complex dielectric function



EELS Spectrum Structure — Core-Loss





EELS Ionization Edges



Williams and Carter (2nd edition)

• EELS edges are classified according to the initial state of the excited electron (K, L, M, ...)



- The edges suitable for EELS analysis for all the elements
- EELS works extremely well with light elements
- Highly complementary to EDS

Core level ionization



https://eels.info/

Core-loss spectrum (> ~ 50 eV)

From interactions with tightly bound inner-shell electrons (coreshell) of the specimen atoms (ionization)

- Core-Loss edge
 - elemental identification/composition
- Near edge fine structure (ELNES):

information about electronic structure (bonding, density of states)

Extended fine structures (EXELFS)

— atom-specific radical distribution of near neighbors
(RDF — Radial-Distribution Function)

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Correlations of Core-loss EELS Features With Specimen Atomic Structure



- The edge onset is characteristic of elements
 element identification
- Core shell electrons can only be excited to:

1. the unoccupied states above the Fermi level (ELNES)

 the possible energy transfer values are controlled by the energy distribution of these available states

exploring unoccupied density of states/bonding

2. "free" electron states if it receives sufficient energy (EXELFS)

exploring distribution of neighboring atoms

 Probability of ionization occurring decreases with energy increasing above E_F

Example of ELNES – White Lines in Transition Metals

Atomic nr	21	22	23	24	25	26	27	28	29	30
Element	Sc	Ti	V	Cr	Mn	Fe	Со	Ni	Cu	Zn
Electron configuration	3 <mark>d¹</mark> 4s²	3 <mark>d²</mark> 4s²	3 <mark>d³</mark> 4s²	3 <mark>d⁵4s1</mark>	3 <mark>d⁵4s²</mark>	3 <mark>d⁶4s²</mark>	3 <mark>d⁷</mark> 4s²	3 <mark>d⁸4s²</mark>	3 <mark>d¹⁰4s¹</mark>	3 <mark>d¹⁰4s²</mark>

- For 3d transition metal, the white lines are corresponding to the transitions of 2p electrons to the partially unoccupied 3d-states.
- The d bands are energetically narrow, leading to sharp peaks
- There is a systematic variation in the intensity as a function of the number of d electrons. Therefore, the intensity can be related to the d bands occupancy (oxidation state)
- In Cu and Zn, 3d bands are fully occupied, so there are no white lines in the spectrum.
- Same happens to 4d transition metals



en.wikipedia.org/wiki/Transition metal

EELS Near Edge Structure (ELNES) — Chemical Bonding



Spectrum Imaging: Building a 3D Dataset



STEM Spectrum Imaging

- Acquired by stepping a focused electron beam
- At each step, a spectrum is recorded along with ADF signal to fill the data cube
- Each image pixel carries a spectrum



Gatan Spectrum imaging fundamentals

Collect and store detailed spatial & spectroscopy info together in a data cube

Allows processing decisions after acquisition!

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Atomic Resolution EELS Mapping



Much faster than EDS mapping owing to a close to 100 % collection efficiency



Atomic Resolution EELS Mapping







Chemical Phase Mapping

Multiple linear least squares (MLLS) method can be used to map overlapping features

$$F(E) = AE^{-r} + B_a S_a(E) + B_b S_b(E) + \dots$$

 $S_a(E)$, $S_b(E)$... — reference models B_a , B_b ... — Scaling coefficients



https://eels.info/



Four-dimensional Scanning Transmission Electron Microscopy (4D-STEM)



Colin Ophus, Microanal, Volume 25, Issue 3, 1 June 2019, Pages 563–582

- Record diffraction pattern for each STEM pixel
 - Extract structural info from the dataset
- Requires high sensitivity, speed & dynamic range detectors
 - Powerful computers

(more memory, high data transfer speed)

• Data analysis algorithms



Electron Microscope Pixel Array Detector

Applications:

- Virtual imaging
- Orientation mapping
- Strain mapping
- Differential phase contrast imaging
- Electron ptychography and more ...

Example of 4D-STEM Applications – Virtual Imaging



Barnaby D.A. Levin, et. al., "4D STEM with a direct electron detector" https://analyticalscience.wiley.com/content/article-do/4d-stem-direct-electron-detector#was.auth.LevinB

Applying virtual detectors to reconstruct STEM images SrTiO₃ along <110>

Example of 4D-STEM Applications – Virtual Imaging



Virtual selected area diffraction Generated from ROIs in real space Using virtual selected area apertures Sum the diffraction patterns from multiple real space probe positions (pixels) in the 4D dataset



Virtual bright/dark field image Generated from ROIs in diffraction space Using virtual objective apertures Sum the intensities of a subset of pixels in the diffraction space, assign it to corresponding pixels in the virtual image

Example of 4D-STEM Applications — Strain Mapping & Orientation Mapping





Colin Ophus, *Microanal, Volume 25, Issue 3, 1 June 2019, Pages 563–582, https://doi.org/10.1017/S1431927619000497

Strain Mapping

Orientation Mapping

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Example of 4D-STEM Applications — Ptychography



- Reconstruct phase info/crystal structure (image) with computational methods
- Spatial resolution improved greatly, beyond traditional STEM imaging techniques

Energy Filtered Transmission Electron Microscopy (EFTEM)



- 1. Unfiltered image or diffraction pattern (DP) is formed
- 2. Image or DP is transformed into the spectrum
- 3. Part of the spectrum is selected by energy-selecting slit
- 4. Selected part of spectrum is transformed back into an energyfiltered image or DP
 - Contrast & resolution enhancement
 - zero-loss imaging
 - pre-carbon imaging
 - most probable loss imaging
 - Element/chemical mapping
 - plasmon peak imaging
 - core-loss edge imaging
 - ELNES mapping

EFTEM – Zero-loss Peak imaging





GΝ

Elastic & inelastic electrons



https://en.wikipedia.org/wiki/Chromatic_aberration



Blocking inelastically scattered electrons





inelastic fog removed

Image courtesy Gatan

EFTEM — Core Loss Edge Imaging



Si K-edge mapping using the three-window method reveals Si at the shell





TEM

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TEMs Equipped with STEM or Analytical Capabilities at MRL



Themis Z STEM/TEM

- 60-300 kV & Energy monochromator
- X-FEG high brightness electron source
- D-Corr spherical aberration probe corrector
- Super-X 4-quandrant SDD EDS detectors
- Gatan GIF Quantum ER image filter and Ultrafast DualEELS
- STEM/TEM Tomography acquisition
- iDPC: Integrated differential phase contrast imaging
- The EMPAD pixelated STEM detector

Aberration Correction, STEM-EELS, STEM-EDS EFTEM, iDPC & 4D-STEM



Talos F200X G2 STEM/TEM

• 80-200 kV

GΝ

- Lorentz Lens for Magnetic samples
- The EMPAD pixelated STEM detector
- The 4D STEM software package
- Super-X SDD EDS detection system
- Segmented Panther STEM detector
- TEM, STEM Tomography, EDS Tomography
- iDPC: Integrated differential phase contrast imaging

STEM-EDS, iDPC & 4D-STEM



H-9500 Dynamic Environmental TEM

- 100-300 kV accelerating voltage
- Electron source: LaB6 (DC heating) Filament
- ETEM: gas injection system
- D-TEM: Gatan K2-IS direct electron camera
- Gatan GIF Quantum ER Filter on K2 Camera
- Hitachi in-situ gas injection heating holder
- Hummingbird liquid cell electrochemistry holder
- MEMS Heating Holder (Hitachi Blaze)

EFTEM

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